

ABSTRACT OF THE INVENTION

The present invention includes an embodiment that relates to method of forming an interconnect. The method includes the effect of reducing electromigration in a metallization. An article achieved by the inventive method includes a first interconnect disposed above a substrate; a first conductive diffusion barrier layer disposed above and on the first interconnect; an upper interconnect, that is either landed or unlanded and that is disposed above the first interconnect; and an upper conductive diffusion barrier layer disposed above and on the upper interconnect.

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